Transistors Panasonic

## 2SC1318

### Silicon NPN epitaxial planar type

For low-frequency power amplification and driver amplification Complementary to 2SA0720

#### ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Complementary pair with 2SA0720

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	7	V	
Collector current	$I_{C}$	0.5	A	
Peak collector current	$I_{CP}$	1	A	
Collector power dissipation	P <sub>C</sub>	625	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C ,	

#### ■ Package

- Code
  - TO-92B-B1
- Pin Name
  - 1. Emitter
  - 2. Collector
  - 3. Base

### ■ Electrical Characteristics $T_a = 25$ °C±3°C

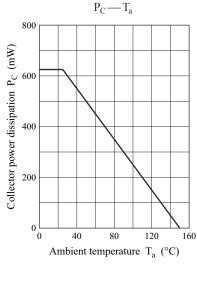
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = 10  \mu A, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	50	0//		V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_E = 10 \mu A, I_C = 0$	70	/		V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$	60.		0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	85		340	
	h <sub>FE2</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 500 \text{ mA}$	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		0.35	0.60	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		1.1	1.5	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>re</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6	15	pF

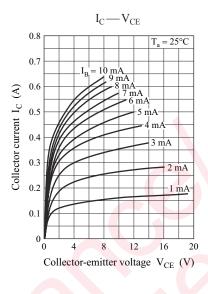
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

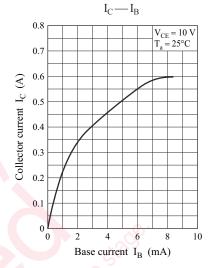
#### 2. \*: Rank classification

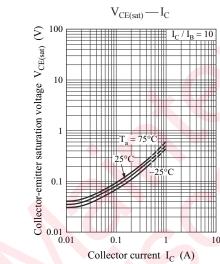
Rank	Q	R	S	
$h_{\mathrm{FE1}}$	85 to 170	120 to 240	170 to 340	

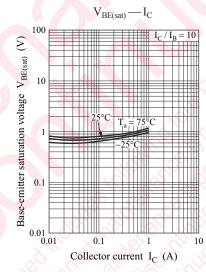
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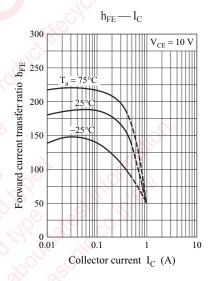


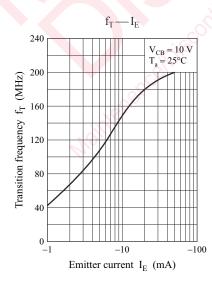


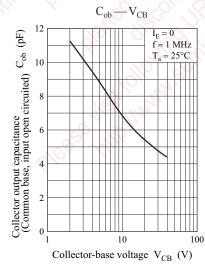


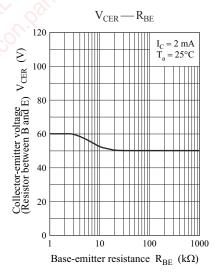






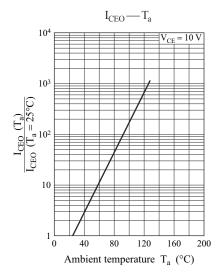


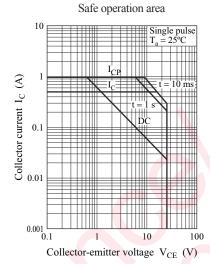




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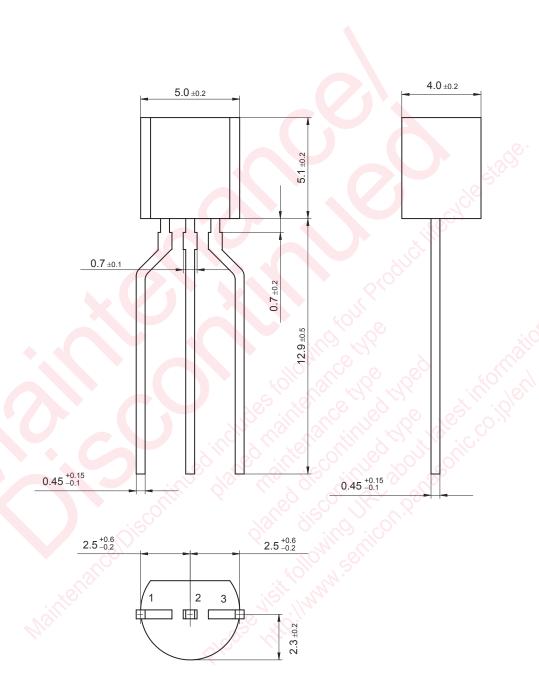




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TO-92-B1 Unit: mm



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